

IN THE SPECIFICATION:

Please amend the paragraphs on page 11 of the Substitute Specification, starting on line 8 and extending to line 20 to read as follows:

--An ITO layer 22 having a thickness of approximately 100 nm is applied onto a glass substrate 21. This layer is then photolithographically structured in such a way that a stripe-shaped structure is produced. A layer 23 of m-TPD having a thickness of approximately 100nm is first applied by thermal evaporation onto the coated substrate pre-treated in this way, followed by a layer 24 of Alq₃ having a thickness of approximately 65nm. An electron transport layer 29 is shown on the layer 24; however, the layer 29 may be omitted.

B1 A layer 25 of LiAlF₄ having a thickness of approximately 1 nm is applied by thermal evaporation onto the layer 29, if it is present, or, if not present, then onto the layer 24, and a layer 26 of aluminum -- serving as a top electrode -- having a thickness of approximately 150 nm is applied onto said layer 25, likewise by thermal evaporation. The two layers 25 and 26 are thereby vapor-deposited through a mask with stripe-shaped openings, corresponding to Example 4, so that organic light-emitting diodes are produced. During operation, the ITO layer is positively contacted and the top electrode is negatively contacted.--
